

SUPPORTING INFORMATION

Thiol-ene Cross-Linked Polymer Gate Dielectrics for Low-Voltage Organic Thin-Film Transistors

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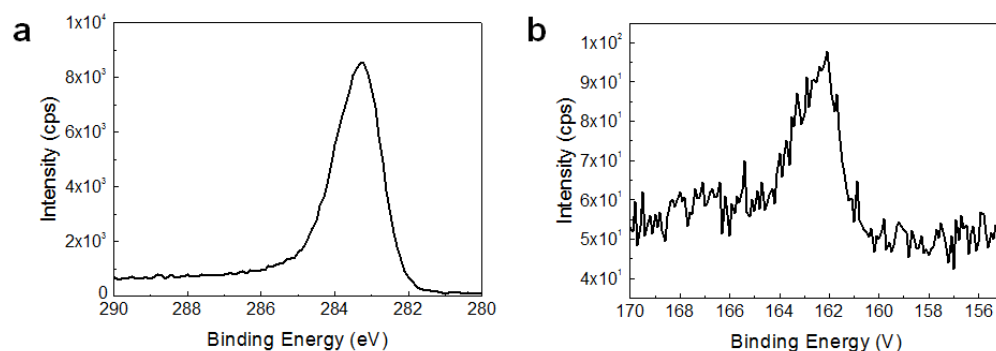


Figure S1. (a) C1s peak and (b) S2p peak of XPS spectra acquired from PVP-4T film after cure

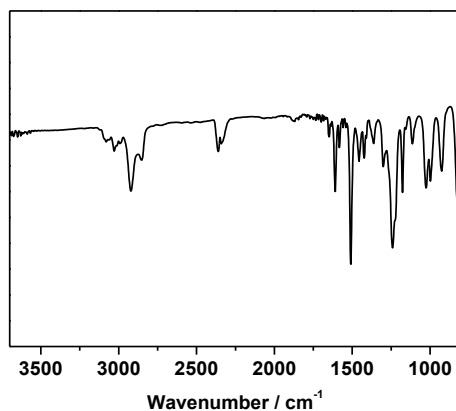


Figure S2: FTIR result of the PVP-alkylene polymer.

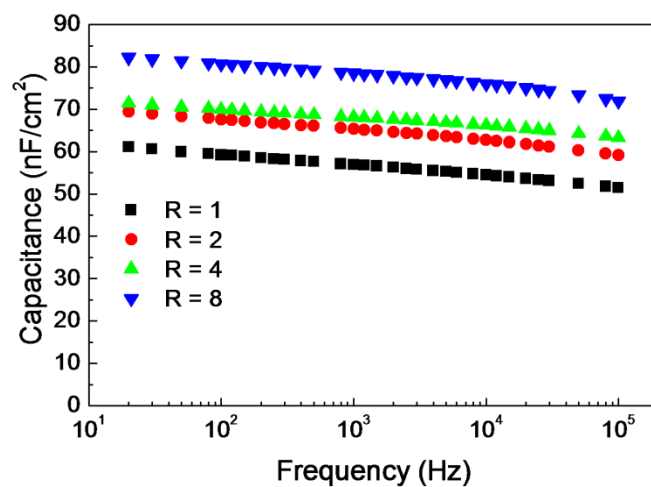


Figure S3. Capacitance vs. frequency for PVP-4T with R=1, 2, 4, and 8

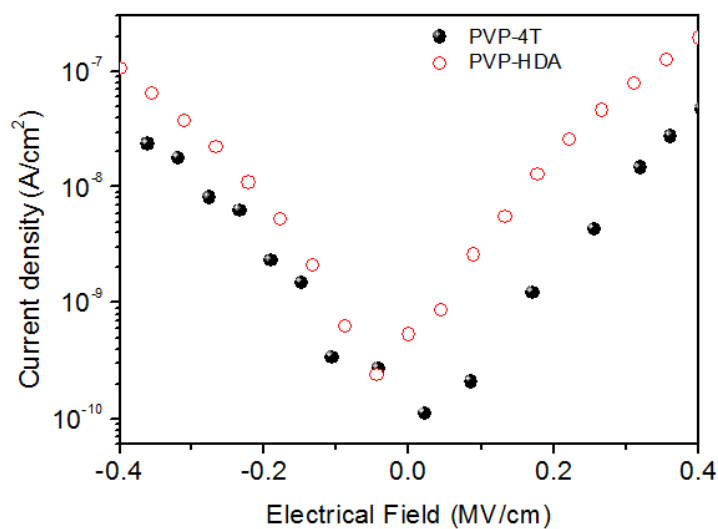


Figure S4. Leakage current for crosslinked PVP-4T and PVP-HDA.

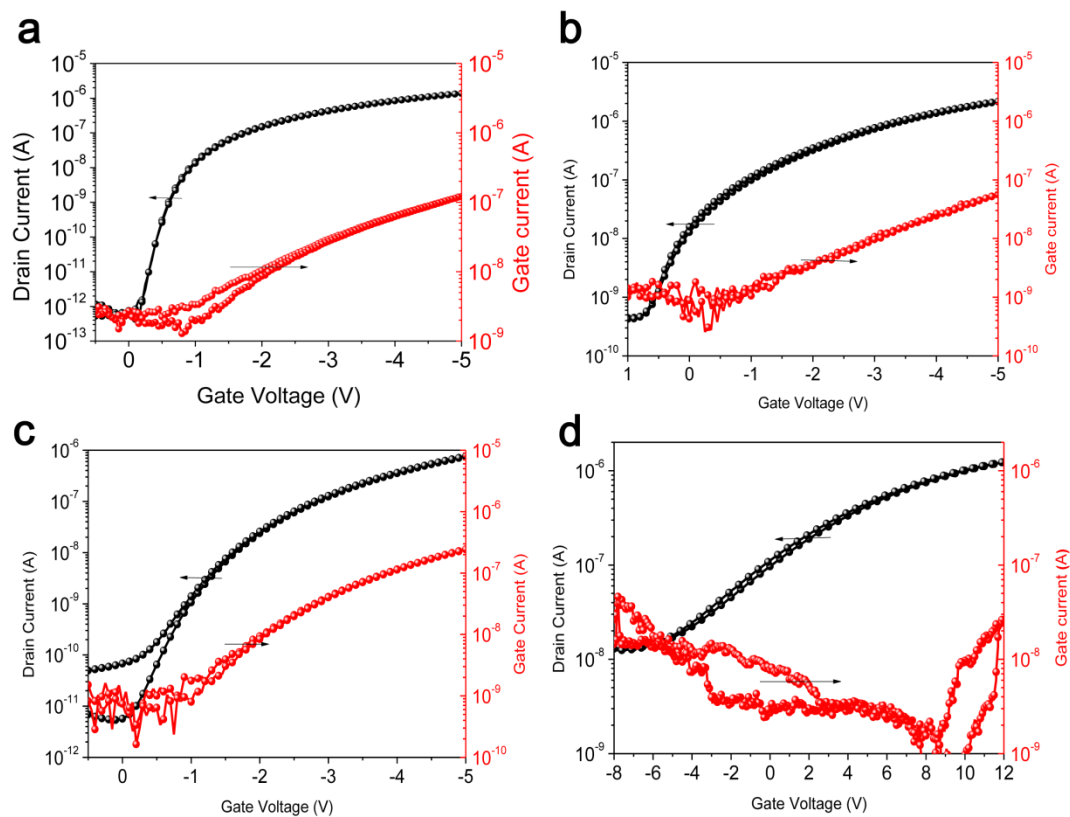


Figure S5. Electrical characteristics of OTFTs based on (a)PTDPPTFT4, (b) TIPS-pentacene, (c) pentacene, and (d) F16-CuPc semiconductors fabricated using the PVP-4T dielectrics.

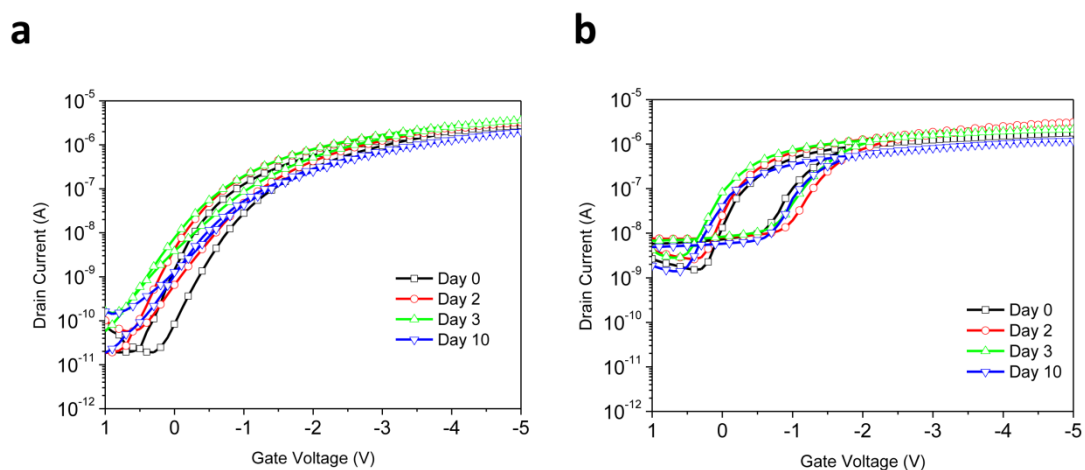


Figure S6. Typical transfer characteristics of OTFT performance of PVP-4T and PVP-HDA with TIPS-pentacene as semiconductor.

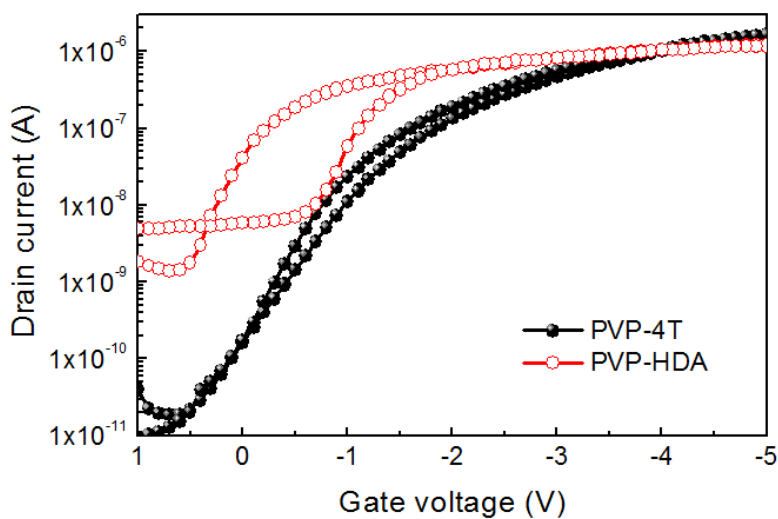


Figure S7. Transfer characteristics of OTFTs based on TIPS-pentacene on PVP-4T and PVP-HDA dielectrics after exposure in the ambient conditions for 10 days.

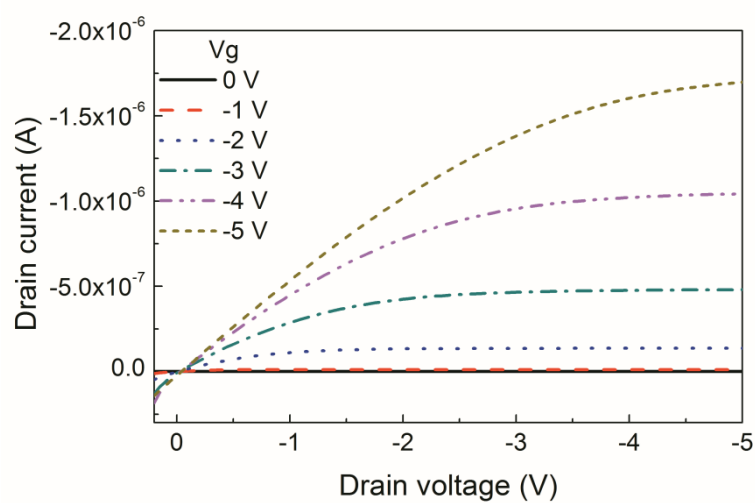
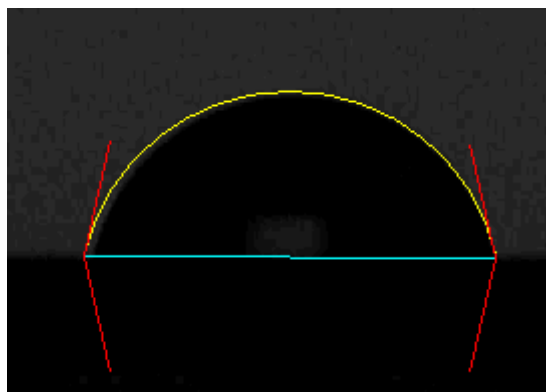


Figure S8. Typical output characteristics of OTFTs of PVP-4T with TIPS-pentacene as semiconductor on Day 10.

(a)



(b)

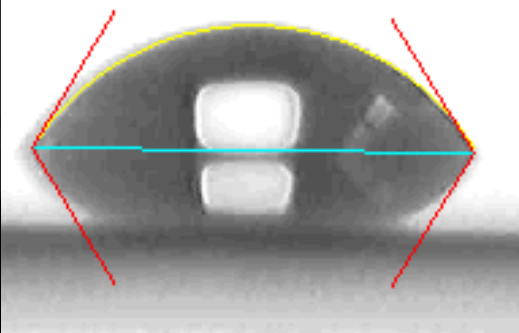


Figure S9. Water contact angles of (a) PVP-4T and (b) PVP-HDA dielectrics.